

FODM8801A, FODM8801B, FODM8801C

OptoHiT™ Series, High-Temperature Phototransistor Optocoupler in Half-Pitch Mini-Flat 4-Pin Package

Features

- Utilizing Proprietary Process Technology to Achieve High Operating Temperature: up to 125°C
- Guaranteed Current Transfer Ratio (CTR) Specifications Across Full Temperature Range
 - Excellent CTR Linearity at High-Temperature
 - CTR at Very Low Input Current, I_F
- High Isolation Voltage Regulated by Safety Agency: C-UL / UL1577, 3750 VAC_{RMS} for 1 minute and DIN EN/IEC60747-5-5
- Compact Half-Pitch, Mini-Flat, 4-Pin Package (1.27 mm Lead Pitch, 2.4 mm Maximum Standoff Height)
- > 5mm Creepage and Clearance Distance
- Applicable to Infrared Ray Reflow, 245°C

Applications

- Primarily Suited for DC-DC Converters
- Ground-Loop Isolation, Signal-Noise Isolation
- Communications – Adapters, Chargers
- Consumer – Appliances, Set-Top Boxes
- Industrial – Power Supplies, Motor Control, Programmable Logic Control

Description

In the OptoHiT™ series, the FODM8801 is a first-of-kind phototransistor, utilizing Fairchild's leading-edge proprietary process technology to achieve high operating temperature characteristics, up to 125°C. The optocoupler consists of an aluminum gallium arsenide (AlGaAs) infrared light-emitting diode (LED) optically coupled to a phototransistor, available in a compact half-pitch, mini-flat, 4-pin package. It delivers high current transfer ratio at very low input current. The input-output isolation voltage, V_{ISO} , is rated at 3750 VAC_{RMS}.

Schematic

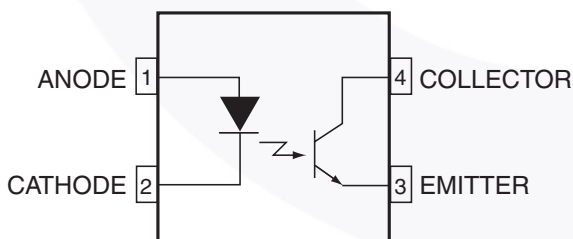


Figure 1. Schematic

Package

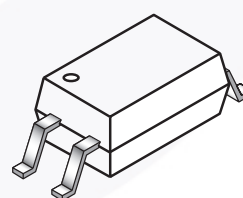


Figure 2. Half-Pitch Mini-Flat

Safety and Insulation Ratings for Half-Pitch Mini-Flat Package

As per DIN EN/IEC 60747-5-5. This optocoupler is suitable for “safe electrical insulation” only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Symbol	Parameter	Min.	Typ.	Max.	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1				
	For rated main voltage < 150 Vrms		I-IV		
	For rated main voltage < 300 Vrms		I-III		
	Climatic Classification		40/125/21		
	Pollution Degree (DIN VDE 0110/1.89)		2		
CTI	Comparative Tracking Index	175			
V _{PR}	Input to Output Test Voltage, Method b, V _{IORM} x 1.875 = V _{PR} , 100% Production Test with t _m = 1 sec, Partial Discharge < 5pC	1060			V _{peak}
V _{PR}	Input to Output Test Voltage, Method a, V _{IORM} x 1.5 = V _{PR} , Type and Sample Test with t _m = 60 sec, Partial Discharge < 5pC	848			V _{peak}
V _{IORM}	Max Working Insulation Voltage	565			V _{peak}
V _{IOTM}	Highest Allowable Over Voltage	4000			V _{peak}
	External Creepage	5			mm
	External Clearance	5			mm
	Insulation thickness	0.5			mm
T _S	Safety Limit Values- Maximum Values allowed in the event of a failure,				
	Case Temperature	150			°C
I _{S,INPUT}	Input Current	200			mA
P _{S,OUTPUT}	Output Power	300			mW
R _{IO}	Insulation Resistance at T _S , V _{IO} =500 V	10 ⁹			Ω

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
TOTAL PACKAGE			
T_{STG}	Storage Temperature	-40 to +150	$^\circ\text{C}$
T_{OPR}	Operating Temperature	-40 to +125	$^\circ\text{C}$
T_J	Junction Temperature	-40 to +140	$^\circ\text{C}$
T_{SOL}	Lead Solder Temperature (Refer to Reflow Temperature Profile on page 13)	260 for 10 s	$^\circ\text{C}$
EMITTER			
$I_{\text{F(average)}}$	Continuous Forward Current	20	mA
V_R	Reverse Input Voltage	6	V
PD_{LED}	Power Dissipation ⁽¹⁾⁽³⁾	40	mW
DETECTOR			
$I_{\text{C(average)}}$	Continuous Collector Current	30	mA
V_{CEO}	Collector-Emitter Voltage	75	V
V_{ECO}	Emitter-Collector Voltage	7	V
PD_C	Collector Power Dissipation ⁽²⁾⁽³⁾	150	mW

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Value	Units
T_A	Operating Temperature	-40 to +125	$^\circ\text{C}$
$V_{\text{FL(OFF)}}$	Input Low Voltage	-5.0 to +0.8	V
I_{FH}	Input High Forward Current	1 to 10	mA

Isolation Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{ISO}	Input-Output Isolation Voltage	$f = 60 \text{ Hz}$, $t = 1 \text{ min.}$, $I_{\text{I-O}} \leq 10 \mu\text{A}^{(4)(5)}$	3,750			VAC_{RMS}
R_{ISO}	Isolation Resistance	$V_{\text{I-O}} = 500 \text{ V}^{(4)}$	10^{12}			Ω
C_{ISO}	Isolation Capacitance	$f = 1 \text{ MHz}$		0.3	0.5	pF

Notes:

- Derate linearly from 73°C at a rate of $0.24 \text{ mW}/^\circ\text{C}$
- Derate linearly from 73°C at a rate of $2.23 \text{ mW}/^\circ\text{C}$.
- Functional operation under these conditions is not implied. Permanent damage may occur if the device is subjected to conditions outside these ratings.
- Device is considered a two-terminal device: pins 1 and 2 are shorted together and pins 3 and 4 are shorted together.
- 3,750 VAC_{RMS} for 1 minute is equivalent to 4,500 VAC_{RMS} for 1 second.

Electrical Characteristics

Apply over all recommended conditions ($T_A = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$ unless otherwise specified).

All typical values are measured at $T_A = 25^{\circ}\text{C}$.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
EMITTER						
V_F	Forward Voltage	$I_F = 1\text{ mA}$	1.00	1.35	1.80	V
$\Delta V_F / \Delta T_A$	Forward-Voltage Coefficient	$I_F = 1\text{ mA}$		-1.6		mV / $^{\circ}\text{C}$
I_R	Reverse Current	$V_R = 6\text{ V}$			10	μA
C_T	Terminal Capacitance	$V = 0\text{ V}$, $f = 1\text{ MHz}$		30		pF
DETECTOR						
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 0.5\text{ mA}$, $I_F = 0\text{ mA}$	75	130		V
BV_{ECO}	Emitter-Collector Breakdown Voltage	$I_E = 100\text{ }\mu\text{A}$, $I_F = 0\text{ mA}$	7	12		V
I_{CEO}	Collector Dark Current	$V_{CE} = 75\text{ V}$, $I_F = 0\text{ mA}$, $T_A = 25^{\circ}\text{C}$			100	nA
		$V_{CE} = 50\text{ V}$, $I_F = 0\text{ mA}$			50	μA
		$V_{CE} = 5\text{ V}$, $I_F = 0\text{ mA}$			30	μA
C_{CE}	Capacitance	$V_{CE} = 0\text{ V}$, $f = 1\text{ MHz}$		8		pF

Transfer Characteristics

Apply over all recommended conditions ($T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$ unless otherwise specified).

All typical values are measured at $T_A = 25^\circ\text{C}$.

Symbol	Parameter	Device	Conditions	Min.	Typ.	Max.	Units
CTR_{CE}	Current Transfer Ratio (Collector-Emitter)	FODM8801A	$I_F = 1.0\text{ mA}, V_{CE} = 5\text{ V}$ @ $T_A = 25^\circ\text{C}$	80	120	160	%
			$I_F = 1.0\text{ mA}, V_{CE} = 5\text{ V}$	35	120	230	%
			$I_F = 1.6\text{ mA}, V_{CE} = 5\text{ V}$	40	125		%
			$I_F = 3.0\text{ mA}, V_{CE} = 5\text{ V}$	45	138		%
		FODM8801B	$I_F = 1.0\text{ mA}, V_{CE} = 5\text{ V}$ @ $T_A = 25^\circ\text{C}$	130	195	260	%
			$I_F = 1.0\text{ mA}, V_{CE} = 5\text{ V}$	65	195	360	%
			$I_F = 1.6\text{ mA}, V_{CE} = 5\text{ V}$	70	202		%
			$I_F = 3.0\text{ mA}, V_{CE} = 5\text{ V}$	75	215		%
		FODM8801C	$I_F = 1.0\text{ mA}, V_{CE} = 5\text{ V}$ @ $T_A = 25^\circ\text{C}$	200	300	400	%
			$I_F = 1.0\text{ mA}, V_{CE} = 5\text{ V}$	100	300	560	%
			$I_F = 1.6\text{ mA}, V_{CE} = 5\text{ V}$	110	312		%
			$I_F = 3.0\text{ mA}, V_{CE} = 5\text{ V}$	115	330		%
$CTR_{CE(SAT)}$	Saturated Current Transfer Ratio (Collector-Emitter)	FODM8801A	$I_F = 1.0\text{ mA}, V_{CE} = 0.4\text{ V}$ @ $T_A = 25^\circ\text{C}$	65	108	150	%
			$I_F = 1.0\text{ mA}, V_{CE} = 0.4\text{ V}$	30	108		%
			$I_F = 1.6\text{ mA}, V_{CE} = 0.4\text{ V}$	25	104		%
			$I_F = 3.0\text{ mA}, V_{CE} = 0.4\text{ V}$	20	92		%
		FODM8801B	$I_F = 1.0\text{ mA}, V_{CE} = 0.4\text{ V}$ @ $T_A = 25^\circ\text{C}$	90	168	245	%
			$I_F = 1.0\text{ mA}, V_{CE} = 0.4\text{ V}$	45	168		%
			$I_F = 1.6\text{ mA}, V_{CE} = 0.4\text{ V}$	40	155		%
			$I_F = 3.0\text{ mA}, V_{CE} = 0.4\text{ V}$	35	132		%
		FODM8801C	$I_F = 1.0\text{ mA}, V_{CE} = 0.4\text{ V}$ @ $T_A = 25^\circ\text{C}$	140	238	380	%
			$I_F = 1.0\text{ mA}, V_{CE} = 0.4\text{ V}$	75	238		%
			$I_F = 1.6\text{ mA}, V_{CE} = 0.4\text{ V}$	65	215		%
			$I_F = 3.0\text{ mA}, V_{CE} = 0.4\text{ V}$	55	177		%
$V_{CE(SAT)}$	Saturation Voltage	FODM8801A	$I_F = 1.0\text{ mA}, I_C = 0.3\text{ mA}$		0.17	0.40	V
			$I_F = 1.6\text{ mA}, I_C = 0.4\text{ mA}$		0.16	0.40	V
			$I_F = 3.0\text{ mA}, I_C = 0.6\text{ mA}$		0.15	0.40	V
		FODM8801B	$I_F = 1.0\text{ mA}, I_C = 0.45\text{ mA}$		0.17	0.40	V
			$I_F = 1.6\text{ mA}, I_C = 0.6\text{ mA}$		0.16	0.40	V
			$I_F = 3.0\text{ mA}, I_C = 1.0\text{ mA}$		0.16	0.40	V
		FODM8801C	$I_F = 1.0\text{ mA}, I_C = 0.75\text{ mA}$		0.18	0.40	V
			$I_F = 1.6\text{ mA}, I_C = 1.0\text{ mA}$		0.17	0.40	V
			$I_F = 3.0\text{ mA}, I_C = 1.6\text{ mA}$		0.17	0.40	V

Switching Characteristics

Apply over all recommended conditions ($T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$ unless otherwise specified).

All typical values are measured at $T_A = 25^\circ\text{C}$.

Symbol	Parameter	Device	Conditions	Min.	Typ.	Max.	Units
t_{ON}	Turn-On Time	All Devices	$I_F = 1.6\text{ mA}$, $V_{CC} = 5\text{ V}$, $R_L = 0.75\text{ k}\Omega$	1	6	20	μs
			$I_F = 1.6\text{ mA}$, $V_{CC} = 5\text{ V}$, $R_L = 4.7\text{ k}\Omega$		6		μs
t_{OFF}	Turn-Off Time	All Devices	$I_F = 1.6\text{ mA}$, $V_{CC} = 5\text{ V}$, $R_L = 0.75\text{ k}\Omega$	1	6	20	μs
			$I_F = 1.6\text{ mA}$, $V_{CC} = 5\text{ V}$, $R_L = 4.7\text{ k}\Omega$		40		μs
t_R	Output Rise Time (10% to 90%)	All Devices	$I_F = 1.6\text{ mA}$, $V_{CC} = 5\text{ V}$, $R_L = 0.75\text{ k}\Omega$		5		μs
t_F	Output Fall Time (90% to 10%)	All Devices	$I_F = 1.6\text{ mA}$, $V_{CC} = 5\text{ V}$, $R_L = 0.75\text{ k}\Omega$		5.5		μs
CM_H	Common-Mode Rejection Voltage (Transient Immunity) – Output High	All Devices	$T_A = 25^\circ\text{C}$, $I_F = 0\text{ mA}$, $V_O > 2.0\text{ V}$, $R_L = 4.7\text{ k}\Omega$, $V_{CM} = 1000\text{ V}^{(6)}$, Figure 16		20		$\text{kV} / \mu\text{s}$
CM_L	Common-Mode Rejection Voltage (Transient Immunity) – Output Low	All Devices	$T_A = 25^\circ\text{C}$, $I_F = 1.6\text{ mA}$, $V_O < 0.8\text{ V}$, $R_L = 4.7\text{ k}\Omega$, $V_{CM} = 1000\text{ V}^{(6)}$, Figure 16		20		$\text{kV} / \mu\text{s}$

Note:

6. Common-mode transient immunity at output high is the maximum tolerable positive dV_{CM}/dt on the leading edge of the common-mode impulse signal, V_{CM} , to assure that the output remains high.

Typical Performance Curves

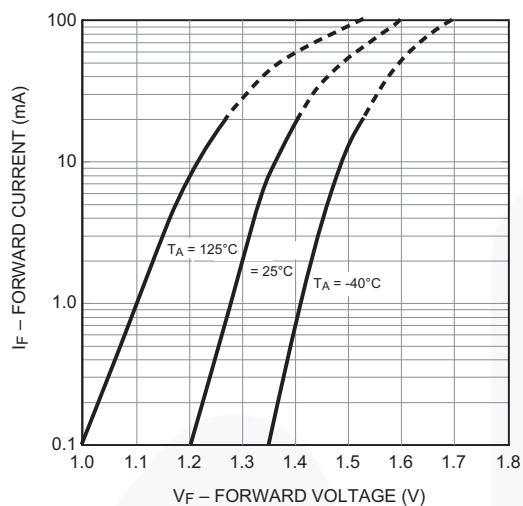


Figure 3. Forward Current vs. Forward Voltage

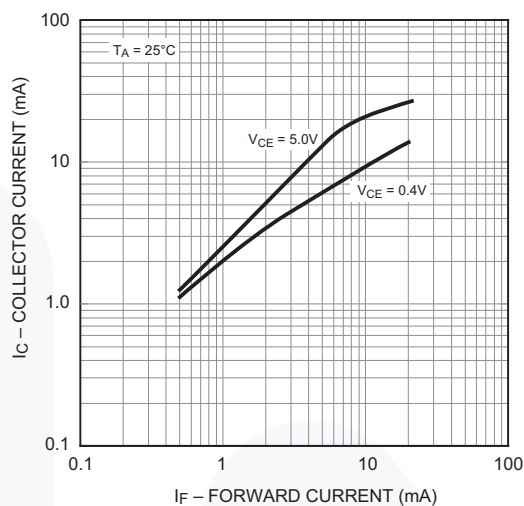


Figure 4. Collector Current vs. Forward Current

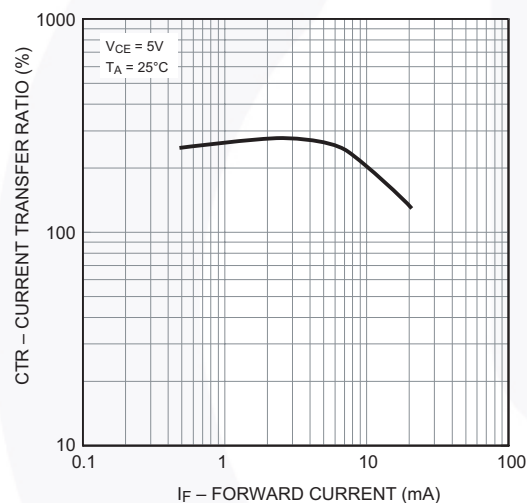


Figure 5. Current Transfer Ratio vs. Forward Current

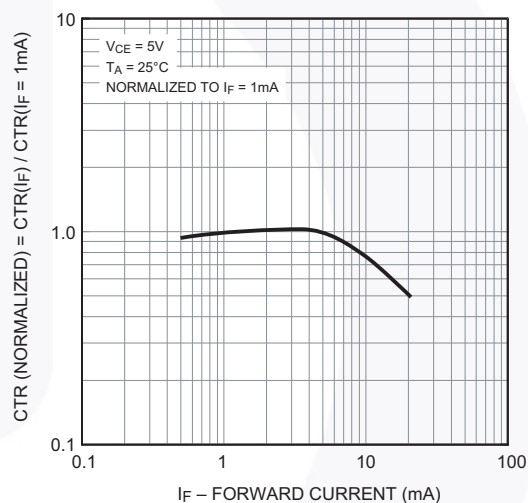


Figure 6. Normalized CTR vs. Forward Current

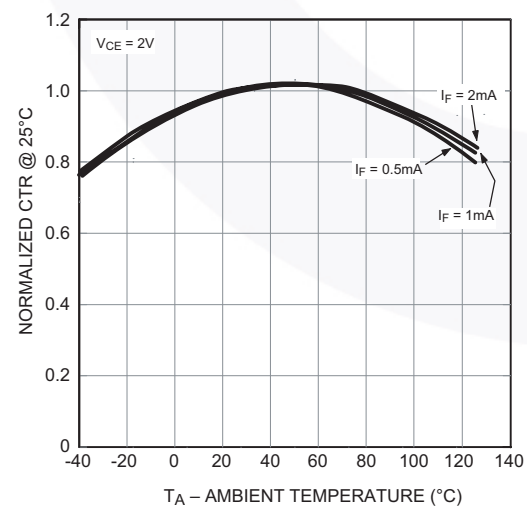


Figure 7. Normalized CTR vs. Ambient Temperature

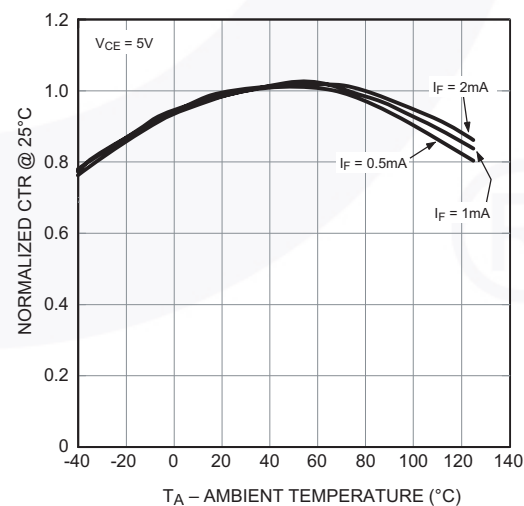


Figure 8. Normalized CTR vs. Ambient Temperature

Typical Performance Curves (Continued)

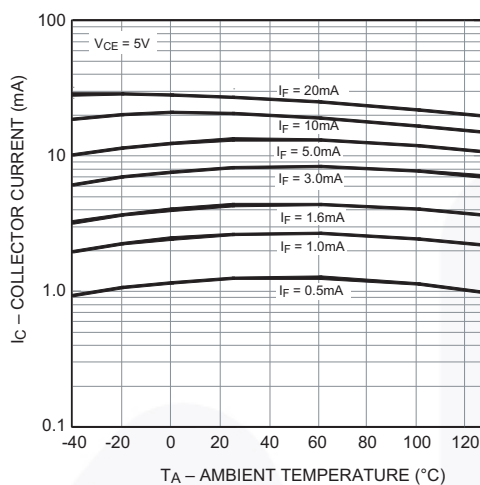


Figure 9. Collector Current vs. Ambient Temperature

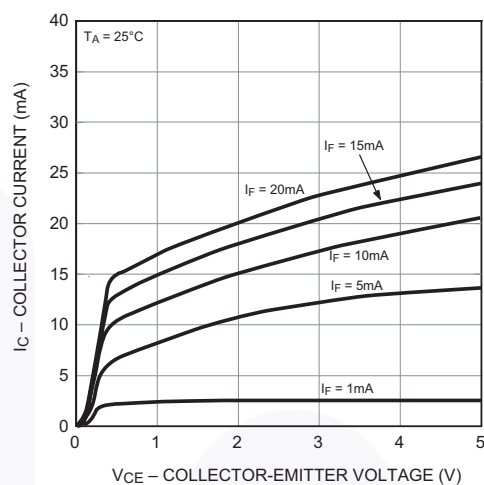


Figure 10 Collector Current vs. Collector-Emitter Voltage

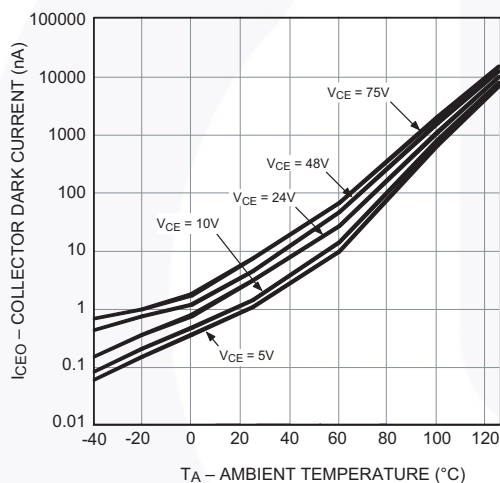


Figure 11. Collector Dark Current vs. Ambient Temperature

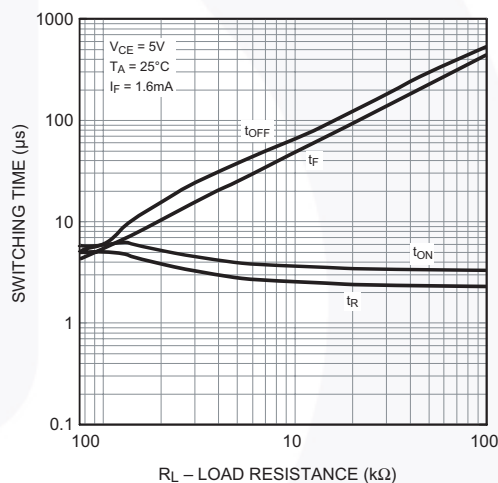


Figure 12. Switching Time vs. Load Resistance

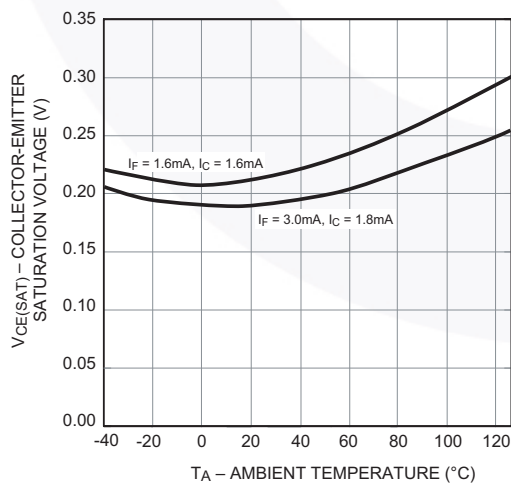


Figure 13. Collector-Emitter Saturation Voltage vs. Ambient Temperature

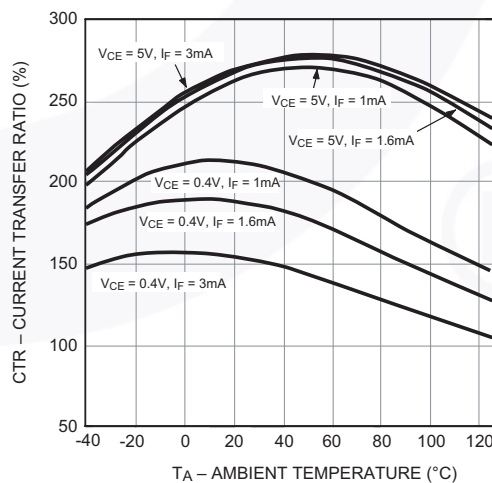


Figure 14. Current Transfer Ratio vs. Ambient Temperature

Test Circuits

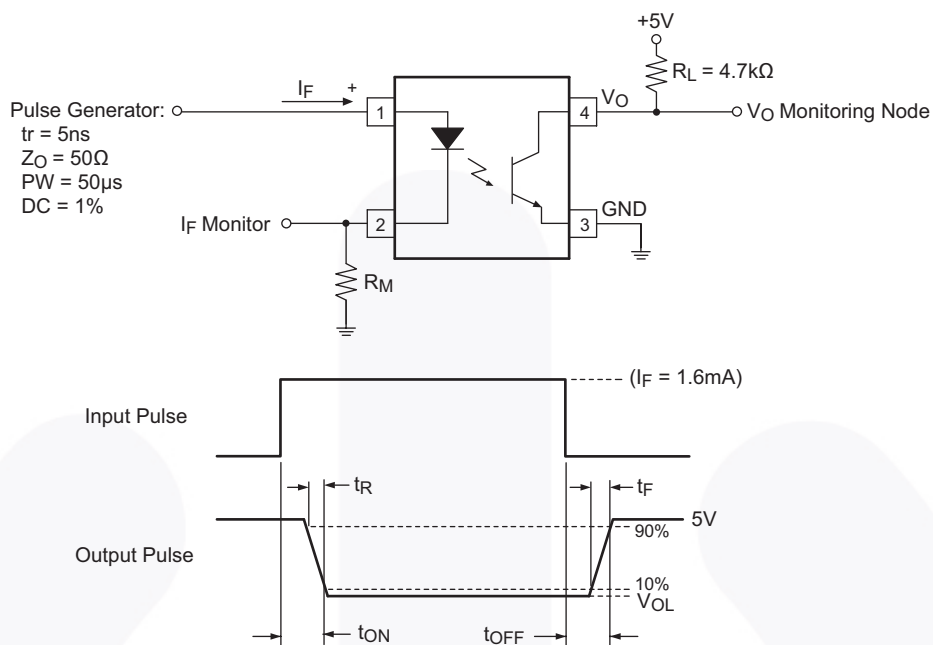


Figure 15. Test Circuit for Propagation Delay, Rise Time, and Fall Time

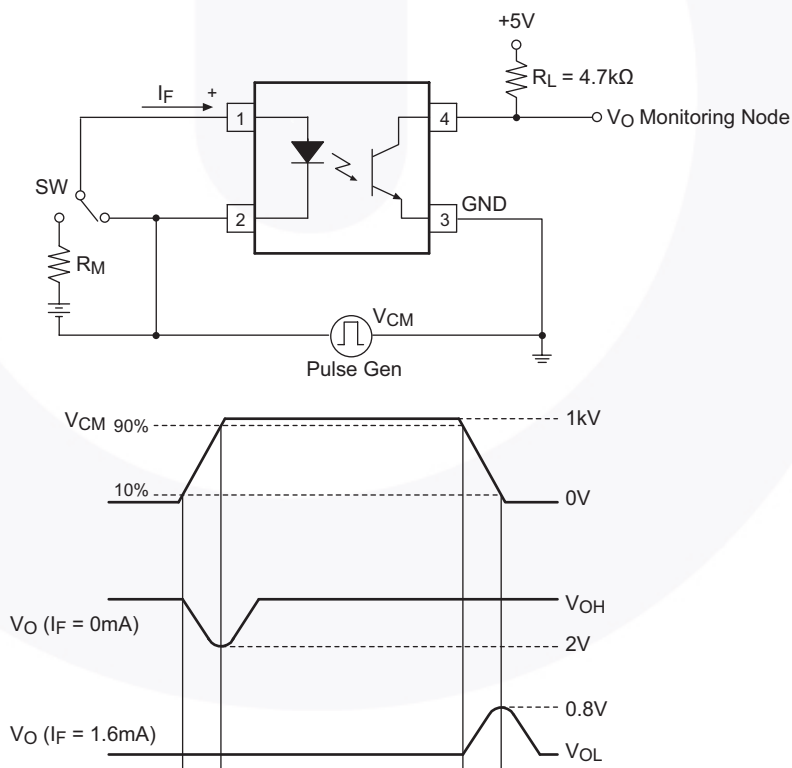
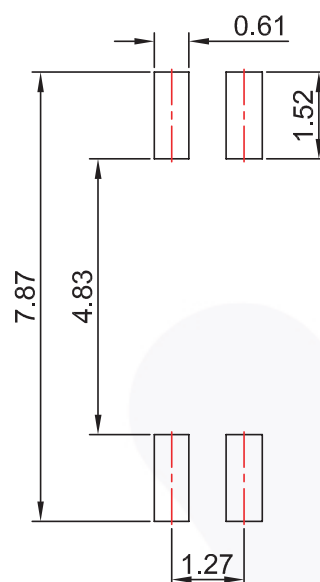
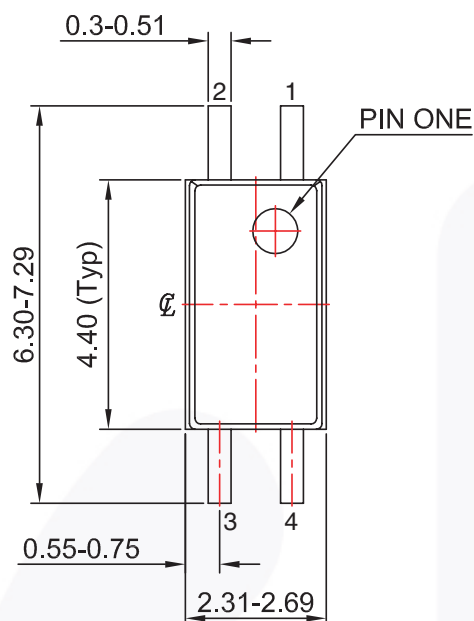
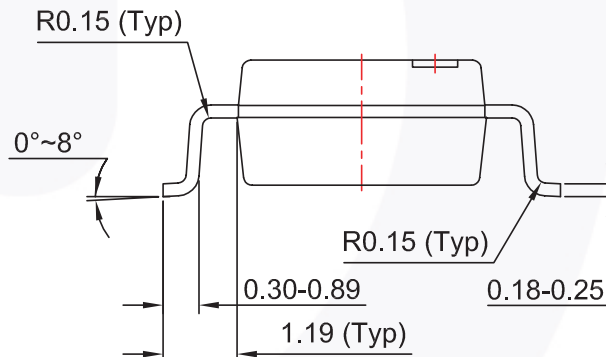
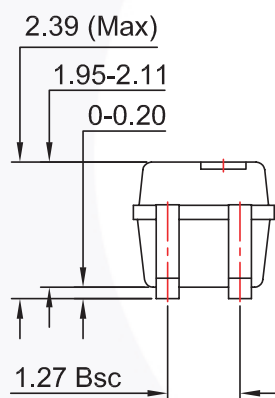


Figure 16. Test Circuit for Instantaneous Common-Mode Rejection Voltage

Package Dimensions



LAND PATTERN RECOMMENDATION



NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS ARE EXCLUSIVE OF BURRS,
MOLD FLASH, AND TIE BAR EXTRUSION
D) DRAWING FILENAME AND REVISION : MKT-MFP04AREV2.

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

<http://www.fairchildsemi.com/packaging/>.

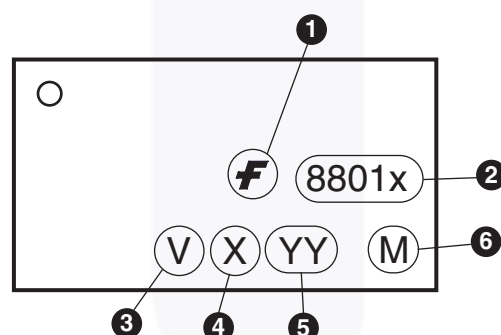
Ordering Information

Part Number	Current Transfer Ratio (CTR %) Option, $I_F = 1\text{ mA}$, $V_{CE} = 5\text{ V}$
FODM8801A	80% to 160%
FODM8801B	130% to 260%
FODM8801C	200% to 400%
Packing Method	
FODM8801x	Tube (100 units per tube)
FODM8801xR2	Tape and Reel (2500 units per reel)
FODM8801xV	Tube (100 units per tube), DIN/EN IEC60747-5-5
FODM8801xR2V	Tape and Reel (2500 units per reel), DIN/EN IEC60747-5-5

 All packages are lead free per JEDEC: J-STD-020B standard.

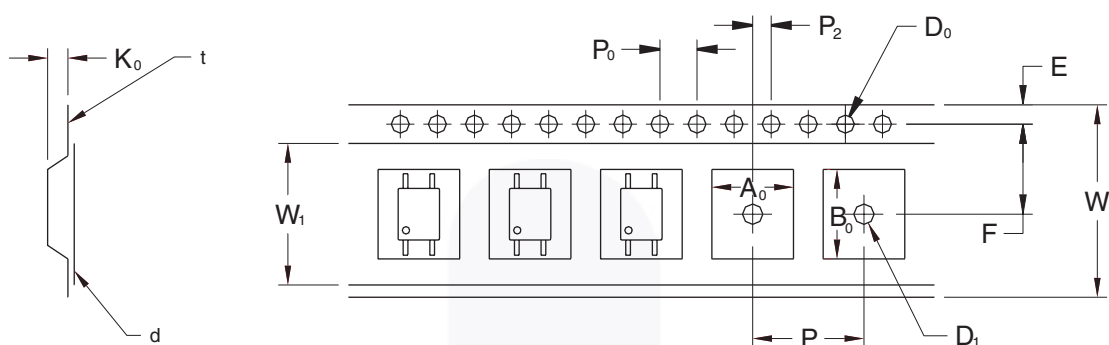
“x” denotes the Current Transfer Ratio option. For example, FODM8801AR2 is a phototransistor with 80% to 160% CTR in tape and reel packaging.

Marking Information



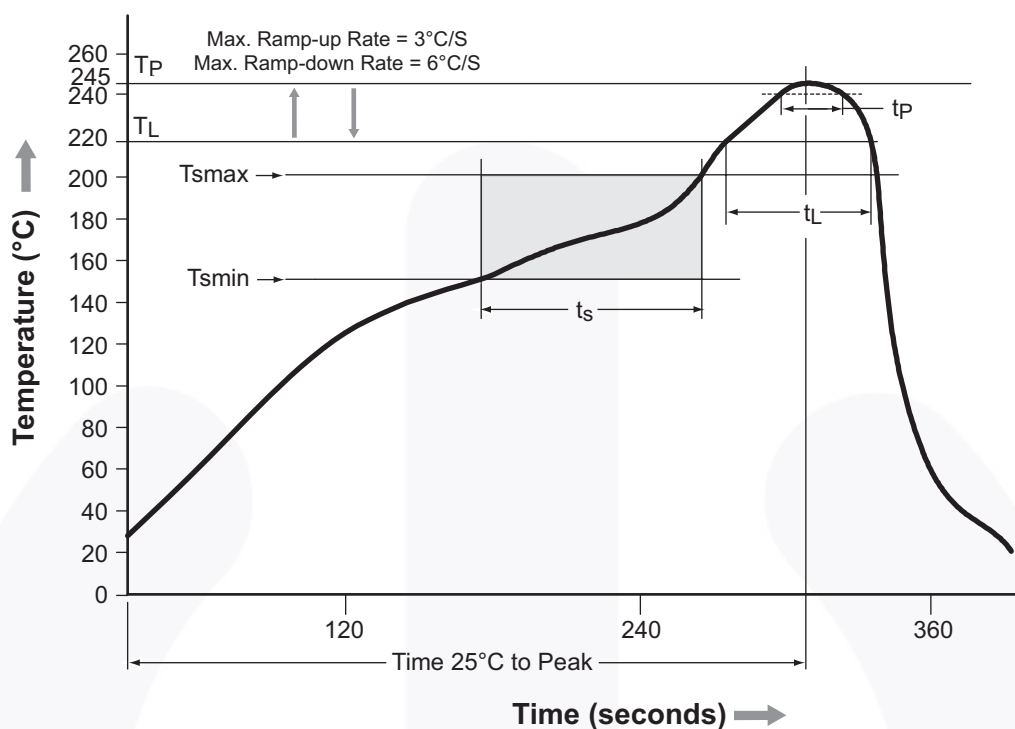
Definitions	
1	Fairchild logo
2	Device number, 'x' denotes CTR% option (A, B, or C)
3	VDE mark (Note: Only appears on parts ordered with DIN/EN IEC60747-5-5 option – See order entry table)
4	One-digit year code, e.g., '1' represents the year 2011
5	Two-digit work week ranging from '01' to '53'
6	Assembly package code

Tape and Reel Dimensions



		1.27 Pitch
Description	Symbol	Dimensions (mm)
Tape Width	W	12.00 +0.30/-0.10
Tape Thickness	t	0.30 ±0.05
Sprocket Hole Pitch	P ₀	4.00 ±0.10
Sprocket Hole Diameter	D ₀	1.50 +0.10/-0.0
Sprocket Hole Location	E	1.75 ±0.10
Pocket Location	F	5.50 ±0.10
	P ₂	2.00 ±0.10
Pocket Pitch	P	8.00 ±0.10
Pocket Dimension	A ₀	2.80 ±0.10
	B ₀	7.30 ±0.10
	K ₀	2.30 ±0.10
Pocket Hole Diameter	D ₁	1.50 Min.
Cover Tape Width	W ₁	9.20
Cover Tape Thickness	d	0.065 ±0.010
Max. Component Rotation or Tilt		10° Max.
Devices Per Reel		2500
Reel Diameter		330 mm (13")

Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60–120 seconds
Ramp-up Rate (tL to tp)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60–150 seconds
Peak Body Package Temperature	245°C +0°C / -5°C
Time (tp) within 5°C of 260°C	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

Figure 17. Reflow Profile



TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

2Cool™	FPS™		Sync-Lock™
AccuPower™	F-PFS™	PowerTrench®	SYSTEM GENERAL®
AX-CAP®*	FRFET®	PowerXS™	TinyBoost™
BitSiC™	Global Power Resource™	Programmable Active Droop™	TinyBuck™
Build it Now™	GreenBridge™	QFET®	TinyCalc™
CorePLUS™	Green FPS™	QS™	TinyLogic®
CorePOWER™	Green FPS™ e-Series™	Quiet Series™	TINYOPTO™
CROSSVOLT™	Gmax™	RapidConfigure™	TinyPower™
CTL™	GTO™		TinyPWM™
Current Transfer Logic™	IntelliMAX™	Saving our world, 1mW/W/kW at a time™	TinyWire™
DEUXPEED®	ISOPLANAR™	SignalWise™	TranSiC™
Dual Cool™	Making Small Speakers Sound Louder and Better™	SmartMax™	TriFault Detect™
EcoSPARK®	MegaBuck™	SMART START™	TRUECURRENT®*
EfficientMax™	MICROCOUPLER™	Solutions for Your Success™	µSerDes™
ESBC™	MicroFET™	SPM®	SerDes™
Fairchild®	MicroPak™	STEALTH™	UHC®
Fairchild Semiconductor®	MicroPak2™	SuperFET®	Ultra FRFET™
FACT Quiet Series™	MillerDrive™	SuperSOT™-3	UniFET™
FACT®	MotionMax™	SuperSOT™-6	VCX™
FAST®	mWSaver™	SuperSOT™-8	VisualMax™
FastvCore™	OptoHiT™	SupreMOS®	VoltagePlus™
FETBench™	OPTOLOGIC®	SyncFET™	XS™
	OPTOPLANAR®		

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Definition of Terms

Datasheet Identification	Product Status	Definition
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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